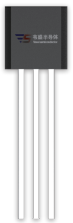
MPS750 TRANSISTOR (PNP)



TO-92

1.EMITTER
2.COLLECTOR
3.BASE

FEATURES

- General Purpose Amplifier

ORDERING INFORMATION

Part Number	Package	Packing Method	Pack Quantity
MPS750	TO-92	Bulk	1000pcs/Bag
MPS750-TA	TO-92	Tape	2000pcs/Box

MAXIMUM RATINGS (T_a=25℃ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	-60	V
V_{CEO}	Collector-Emitter Voltage	-40	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current -Continuous	-2	A
P_C	Collector Power Dissipation	625	mW
$R_{\theta JA}$	Thermal Resistance From Junction To Ambient	200	℃/W
T_J,T_{stg}	Operation Junction and Storage Temperature Range	-55~+150	℃

T_a=25℃ unless otherwise specified

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C= -0.1mA,I_E=0	-60			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$*	I_C=-10mA,I_B=0	-40			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E=-0.01mA,I_C=0	-5			V
Collector cut-off current	I_{CBO}	V_{CB}=-60V,I_E=0			-0.1	μA
Emitter cut-off current	I_{EBO}	V_{EB}=-4V,I_C=0			-0.1	μA
DC current gain	$h_{FE(1)}$*	V_{CE}=-2V, I_C=-50mA	75			
	$h_{FE(2)}$*	V_{CE}=-2V, I_C=-500mA	75		400	
	$h_{FE(3)}$*	V_{CE}=-2V, I_C=-1A	75			
	$h_{FE(4)}$*	V_{CE}=-2V, I_C=-2A	40			
Collector-emitter saturation voltage	$V_{CE(sat)\ (1)}$*	I_C=-2A,I_B=-200mA			-0.5	V
	$V_{CE(sat)\ (2)}$*	I_C=-1A,I_B=-100mA			-0.3	V
Base-emitter saturation voltage	$V_{BE(sat)}$*	I_C=-1A,I_B=-100mA			-1.2	V
Base-emitter voltage	V_{BE}*	I_C=-1A, V_{CE}=-2V			-1.0	V
Transition frequency	f_T	V_{CE}=-5V,I_C=-50mA,f=100MHz	75			MHz

*Pulse test: pulse width ≤300μs, duty cycle≤ 2.0%.